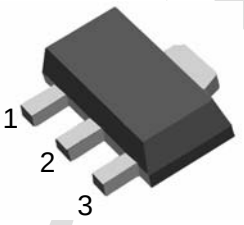
# BCX52 TRANSISTOR (PNP)

**SOT-89**

1. BASE
2. COLLECTOR
3. EMITTER




## FEATURES

Power dissipation

$P_{CM}$: 0.5 W (Tamb=25℃)

Collector current

$I_{CM}$: -1 A

Collector-base voltage

$V_{(BR)CBO}$: -60 V

Operating and storage junction temperature range

$T_J$, $T_{stg}$: -55℃ to +150℃

## ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

| Parameter | Symbol | Test conditions | MIN | MAX | UNIT |
|---|---|---|---|---|---|
| **Collector-base breakdown voltage** | $V_{(BR)CBO}$ | Ic=-100μA , $I_E$=0 | -60 | | V |
| **Collector-emitter breakdown voltage** | $V_{(BR)CEO}$ | $I_C$=-10mA , $I_B$=0 | -60 | | V |
| **Emitter-base breakdown voltage** | $V_{(BR)EBO}$ | $I_E$=-10μA, $I_C$=0 | -5 | | V |
| **Collector cut-off current** | $I_{CBO}$ | $V_{CB}$=-30V, $I_E$=0 | | -0.1 | μA |
| **Emitter cut-off current** | $I_{EBO}$ | $V_{EB}$=-5V, $I_C$=0 | | -0.1 | μA |
| **DC current gain** **BCX52** **BCX52-10** **BCX52-16** | $h_{FE(1)}$ | $V_{CE}$=-2V, $I_C$=-150mA | 63<br>63<br>100 | 250<br>160<br>250 | |
| | $h_{FE(2)}$ | $V_{CE}$=-2V, $I_C$= -5mA | 63 | | |
| | $h_{FE(3)}$ | $V_{CE}$=-2V, $I_C$=-500mA | 40 | | |
| **Collector-emitter saturation voltage** | $V_{CE(sat)}$ | $I_C$=-500 mA, $I_B$=-50mA | | -0.5 | V |
| **Base-emitter voltage** | $V_{BE(ON)}$ | $I_C$=- 500mA, $V_{CE}$=-2V | | -1 | V |
| **Transition frequency** | $f_T$ | $V_{CE}$= -5V, $I_C$= -10mA<br>f = 100MHz | 50 | | MHz |

| **DEVICE MARKING** | BCX52=AE BCX52-10=AG BCX52-16=AM |
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